

Ultrafast laser-induced microplasmas inside band-gap solids

Precision and controllability over the spectrum

David Grojo

25 Octobre 2021

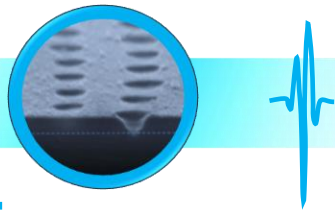
GDR Emili– Journées 2021, Palaiseau

LP3, Marseille, France



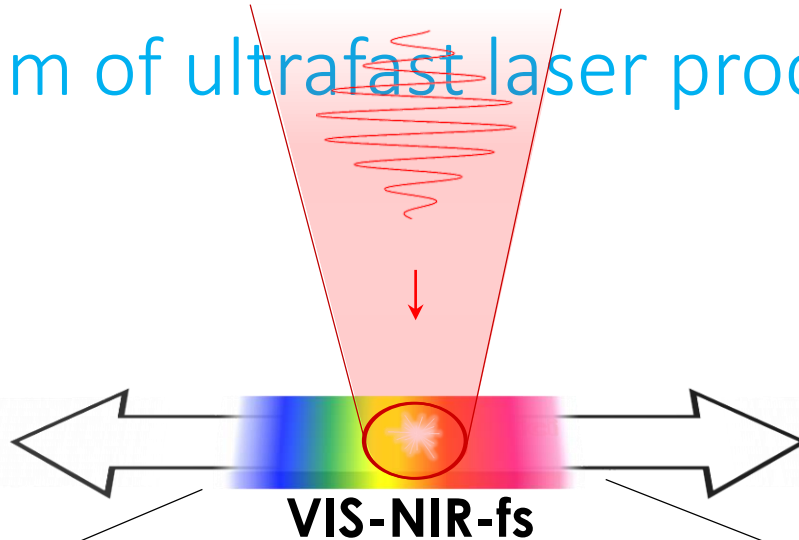
Broadening the spectrum of ultrafast laser processing ?

XUV-as

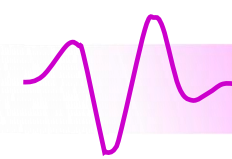


NANOSCALE
PRECISION GUIDING

Ultra-precision
Sub-diffraction
Low thermal budget



VIS-NIR-fs

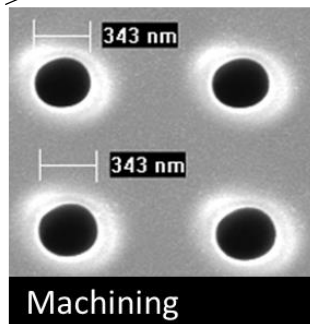


THz



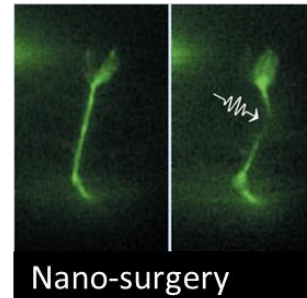
3D IN SILICON
BREAKDOWN IGNITION

Three-dimension
NL/Breakdown processing
in transparent matter



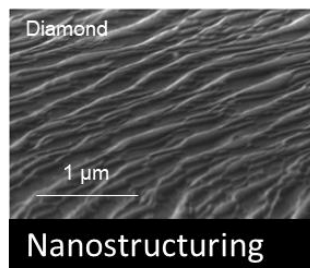
Machining

PNAS 101 (2004) 5856



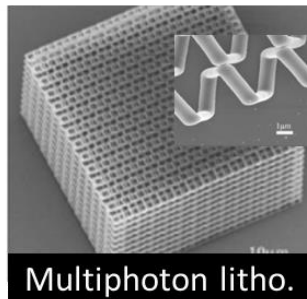
Nano-surgery

Nature 432 (2004) 822



Nanostructuring

Nat Commun 5, 3341 (2014)



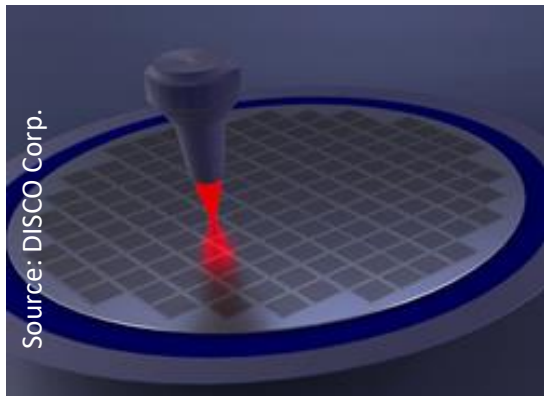
Multiphoton litho.

Adv. Mater. 17, 541-545 (2005)



Simple and robust method for determination of laser fluence thresholds for material modifications **Open Research Europe** 2021, 1:7
Evidencing the nonlinearity independence of resolution in femtosecond laser ablation, **Optics Letters** 45 (2020) 952
Assessing the limits of determinism and precision in ultrafast laser ablation, **Applied Physics Letters** 117 (2020) 171604.

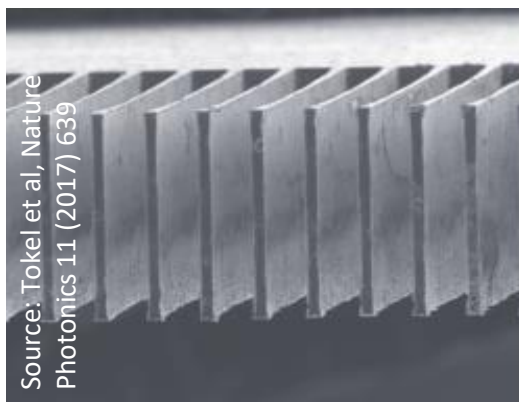
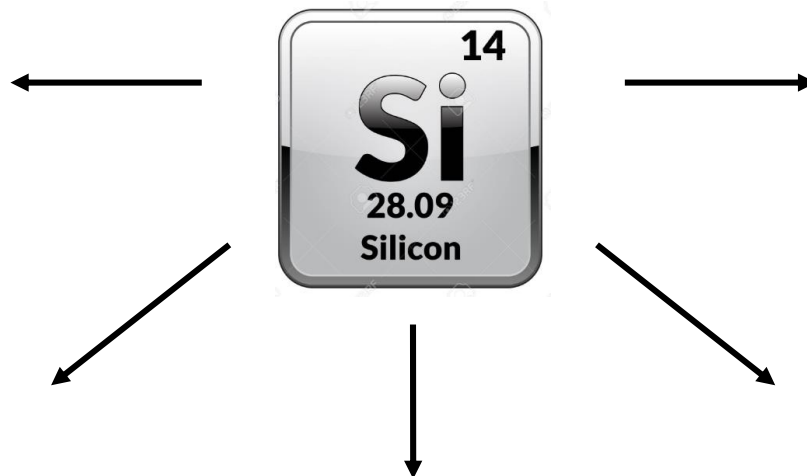
Internal structuring of Silicon using infrared ultrafast lasers ?



Laser chips cutting

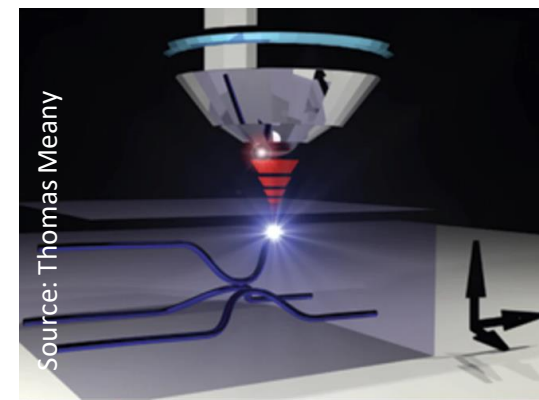


Cooling microfluidic channels

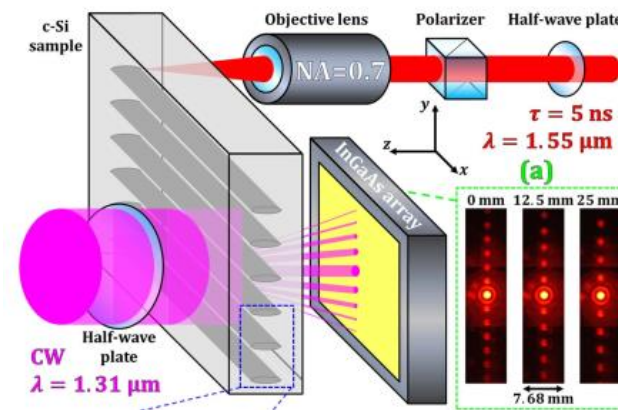


Complex MEMS structures

+ Optics Lett. 44 (2019) 1619-1622



Waveguide writing



Index engineering

Optics Lett. 43 (2018) 6069-6072
+ Optics Lett. 41 (2016) 4875

3D Silicon photonics

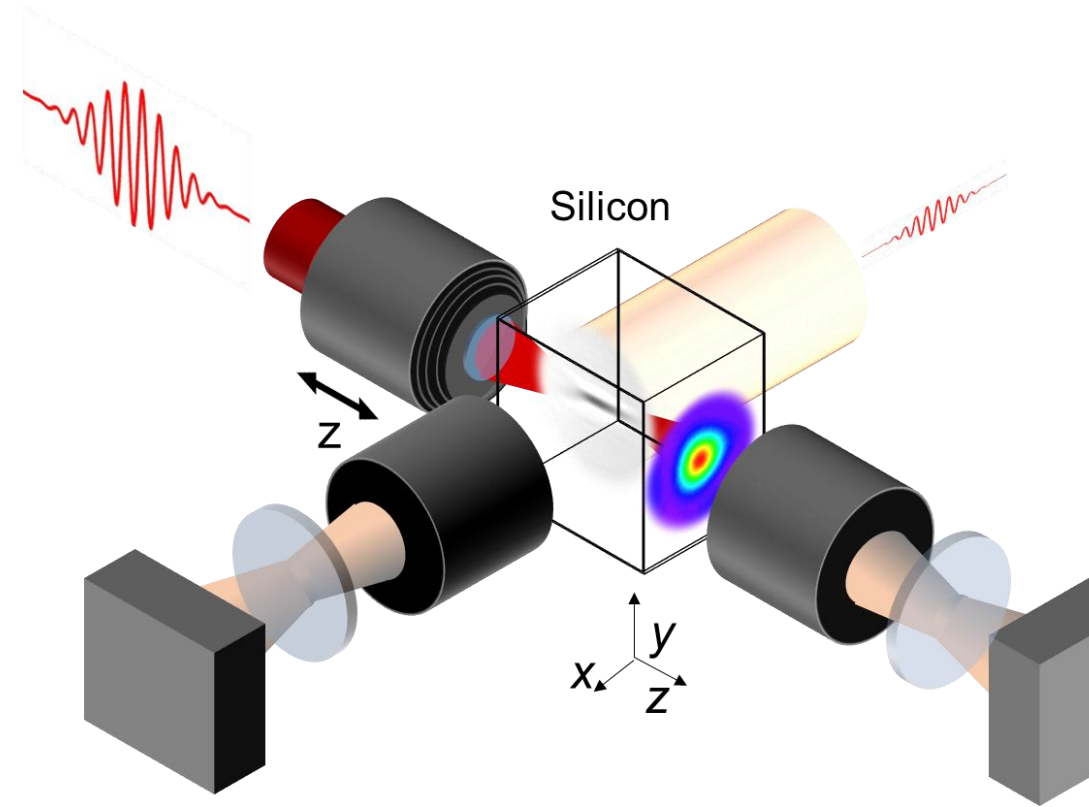
Applications similar to those in transparent dielectrics but much more challenging in Si...

Outline – Ultrafast Laser Writing Deep inside Silicon

1. A challenging problem

2. *Optimizations in the time domain*

3. *Today's performance with introduction multi-timescale control*

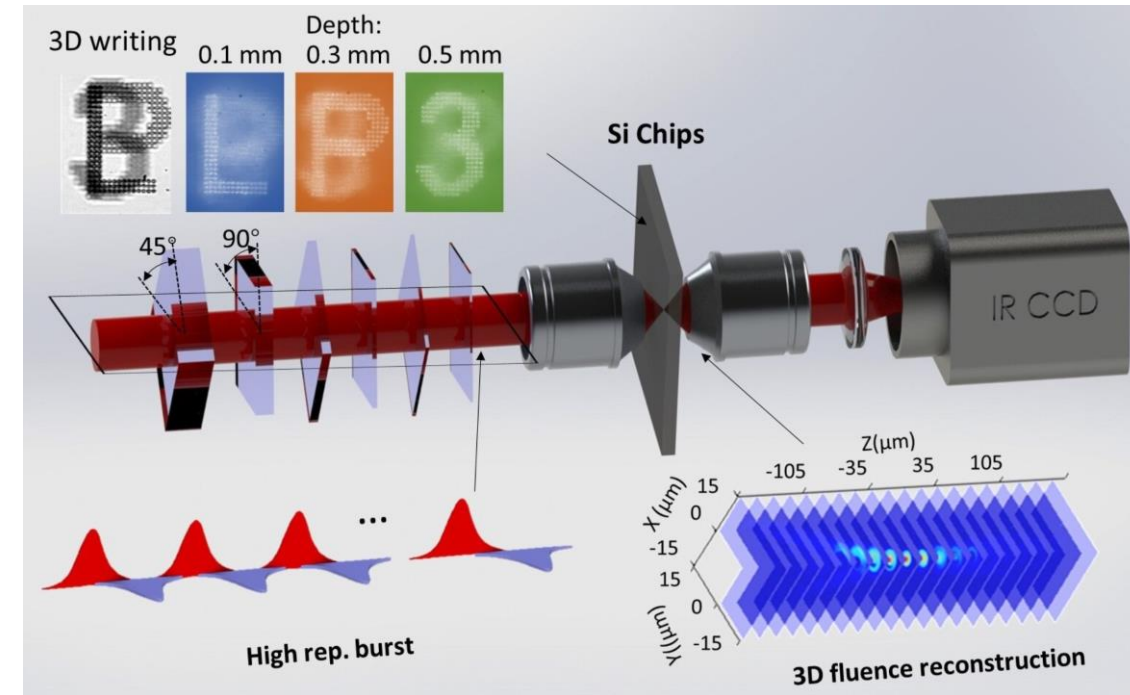


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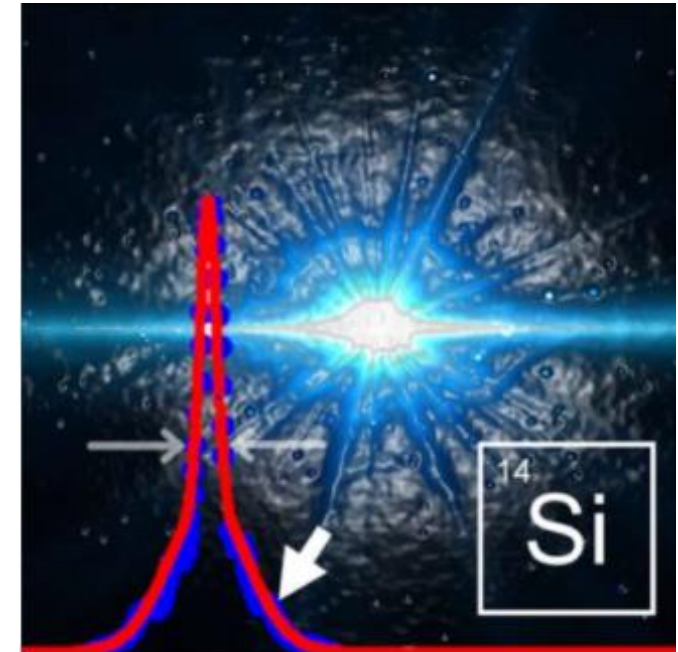


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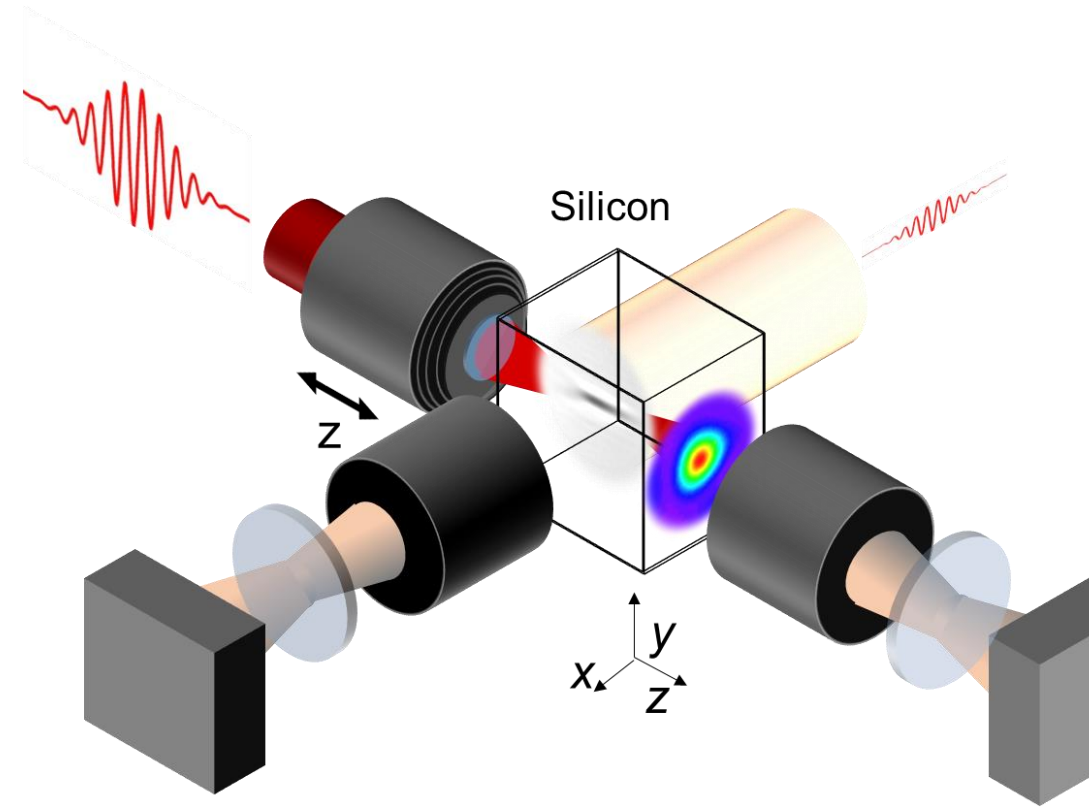


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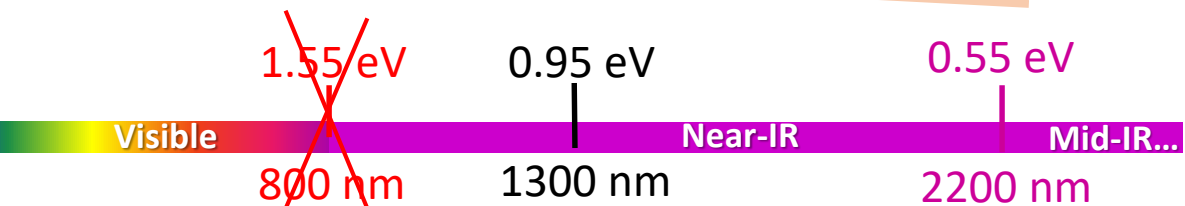
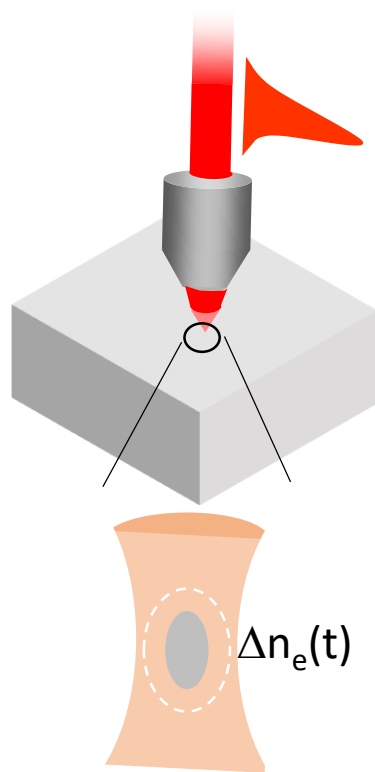
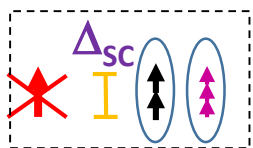
3. Today's performance with introduction multi-timescale control



Challenges for high space-time energy localization in Si



- Indirect band Gap: **1.1 eV**
- $h\nu_{\text{las}} < \text{band gap}$
- **Optical Parametric Amp. (OPA)**
 $\lambda_{\text{las}} > 1.2\mu\text{m}$ ($h\nu_{\text{las}} < 1\text{ eV}$)
 -Tu: or Er: doped fiber lasers



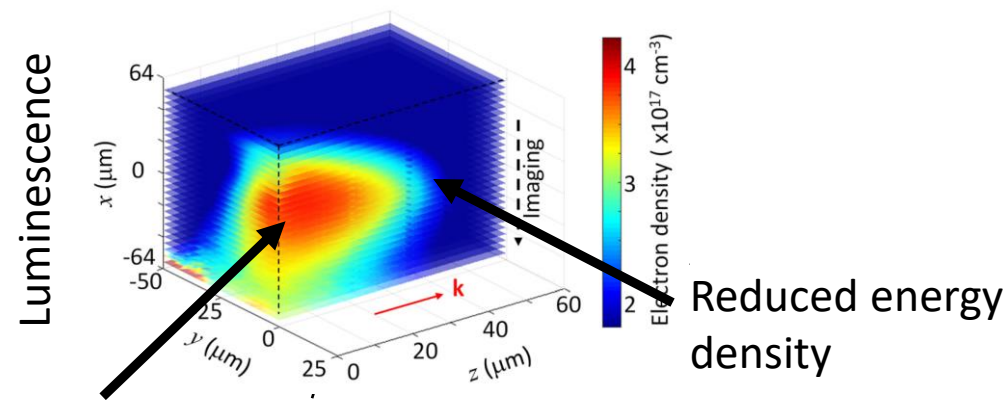
Need for SWIR fs pulses...

Narrow gap

- high index $n=3.5$
- .. and associated refraction
- Increased 2PA absorption coef. ($\approx \text{dielectrics} \times 100$)
- Stronger nonlinearities**

Long wavelengths

- Reduced critical plasma densities ($\approx \text{visible}/10-100$)
- Stronger plasma effects**



Detrimental pre-focal plasmas

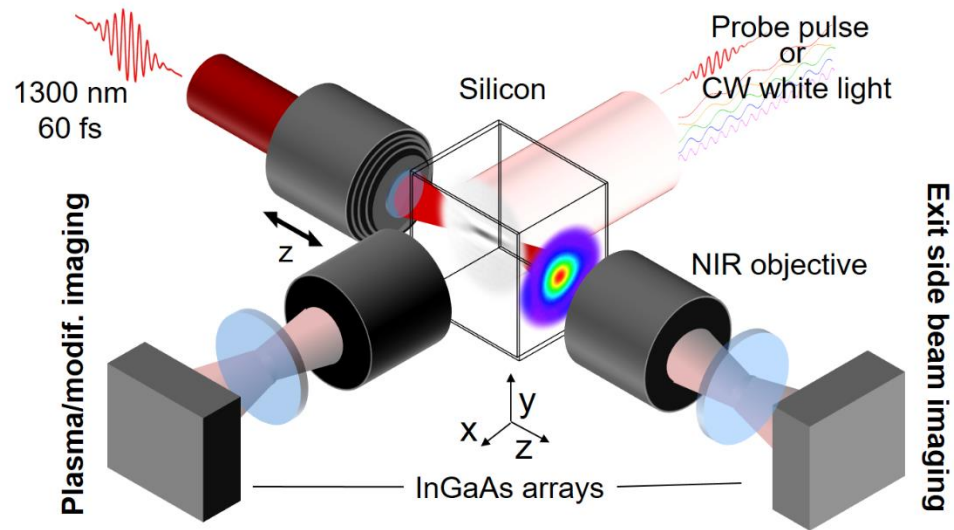
Applied Physics Letters 119 (2021) 041108

Delocalization preventing excitation ...

Accessing extreme spatio-temporal energy localizations in Si

Experimental

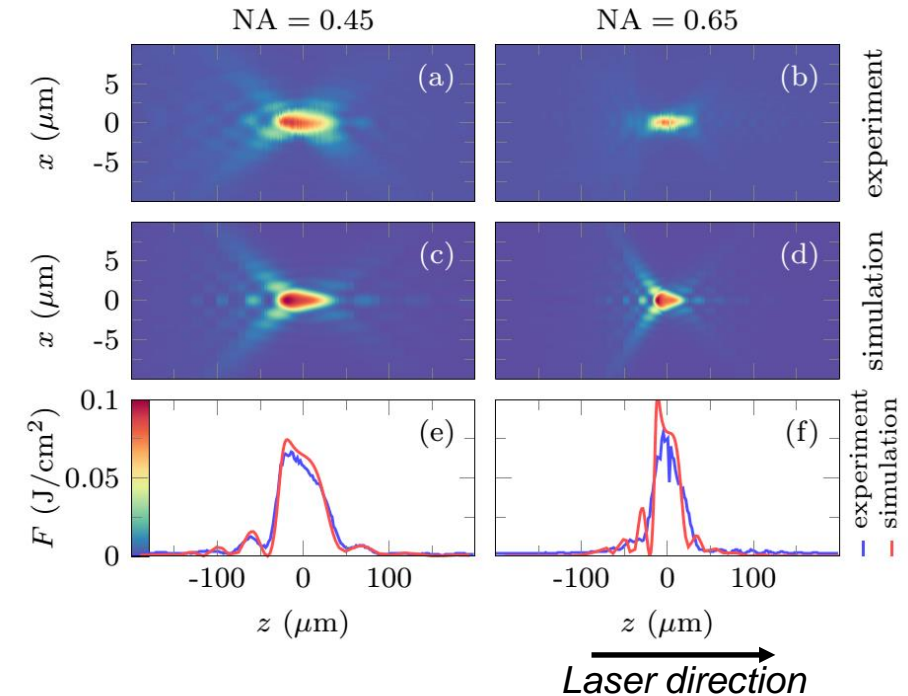
Full space-time IR microscopy of the **beam (3D)** and matter



Nature Communications 8 (2017) 773

Modeling

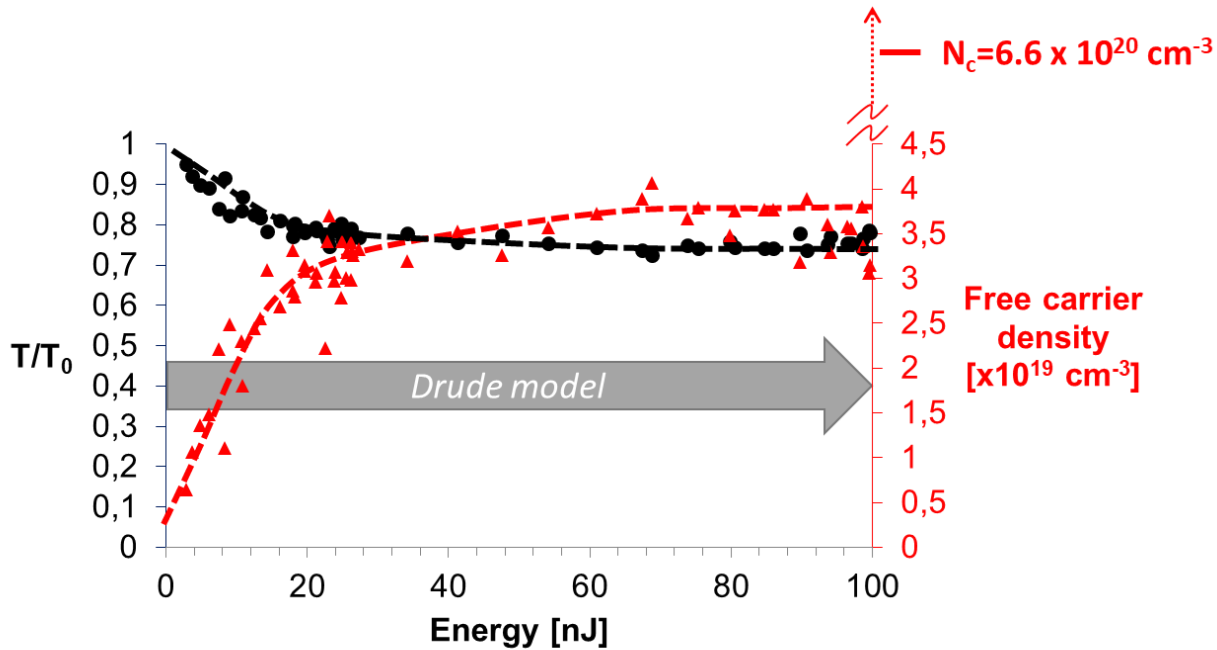
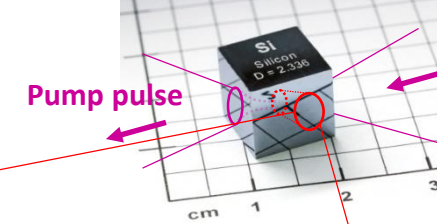
Transformation optics enabling the use of scalar equations for **non-paraxial** propagation problems



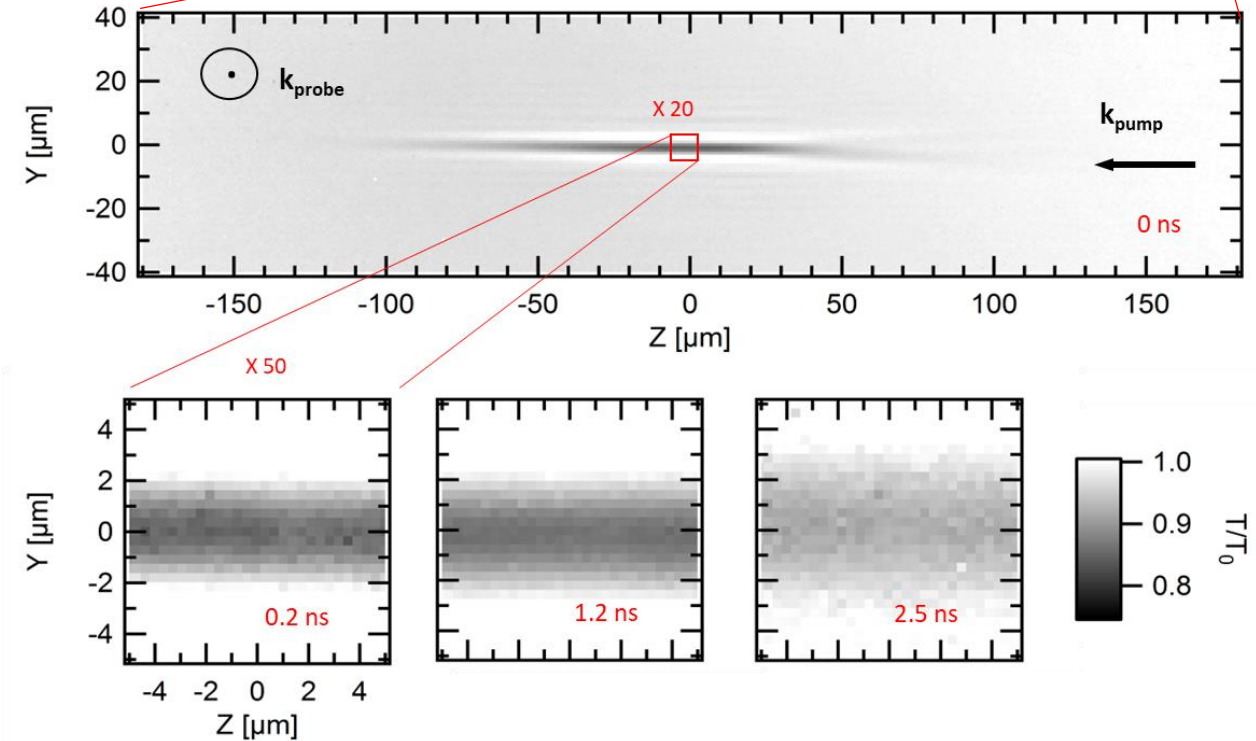
Physical Review Letters 117 (2016) 043902

Experimental and numerical tools for studying the physical mechanisms taking place in the nonlinear interactions (propagation, ionization, plasma, etc..)

Ultrafast microscopy of plasmas inside Si



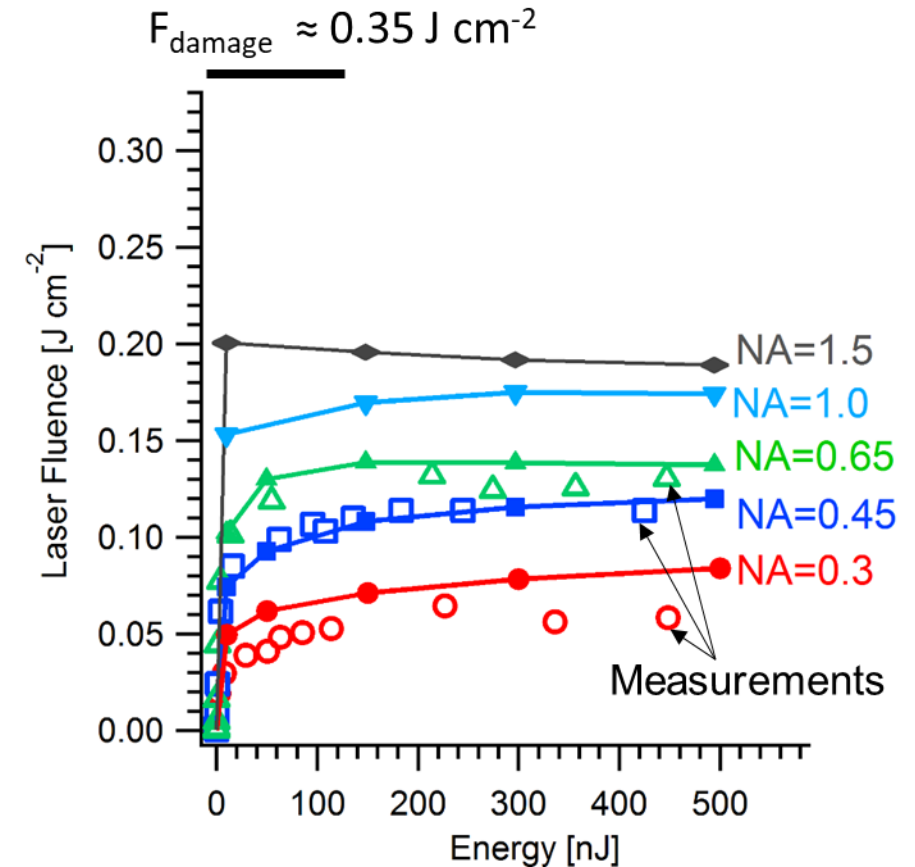
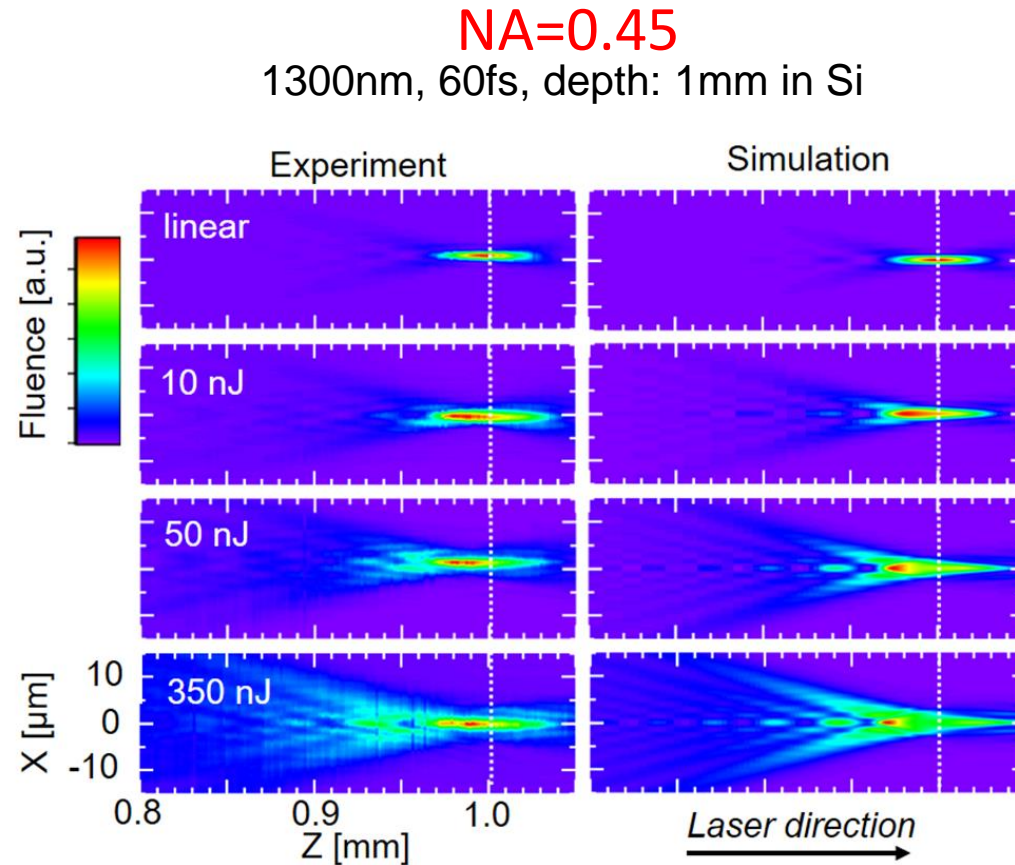
Appl. Phys. Lett. 105, 191103 (2014)



Appl. Phys. Lett. 108 (2016) 041107

Self-limited nonlinear excitation but no evidence of ultrafast dissipation (ns carrier diffusion) which could limit the achievable energy density!

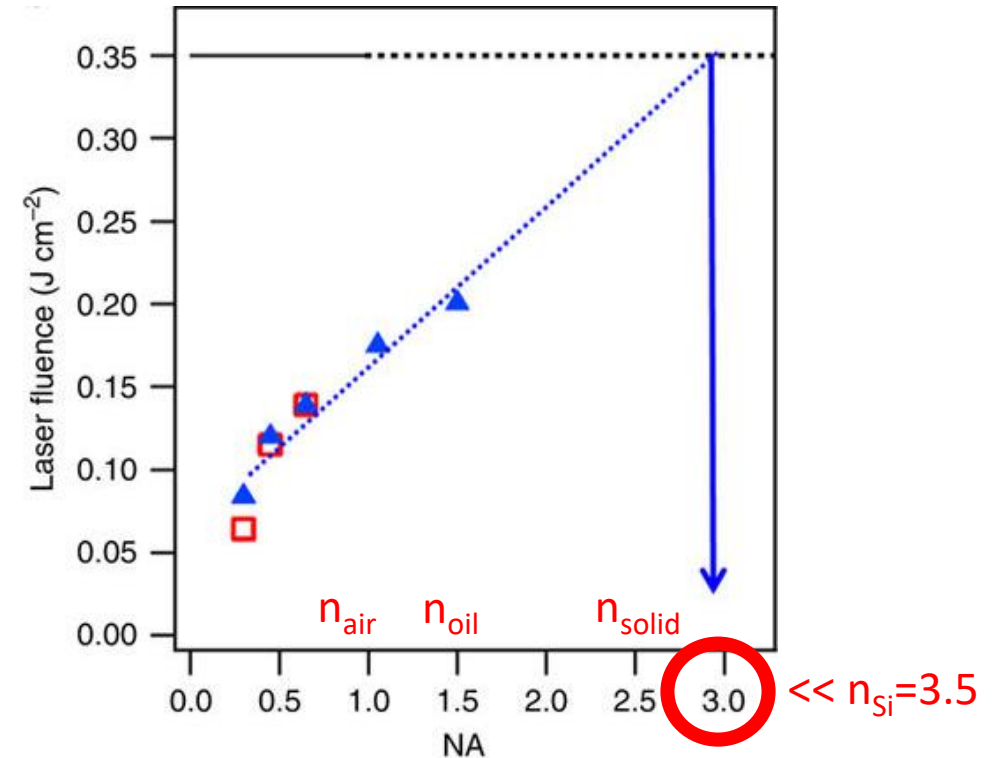
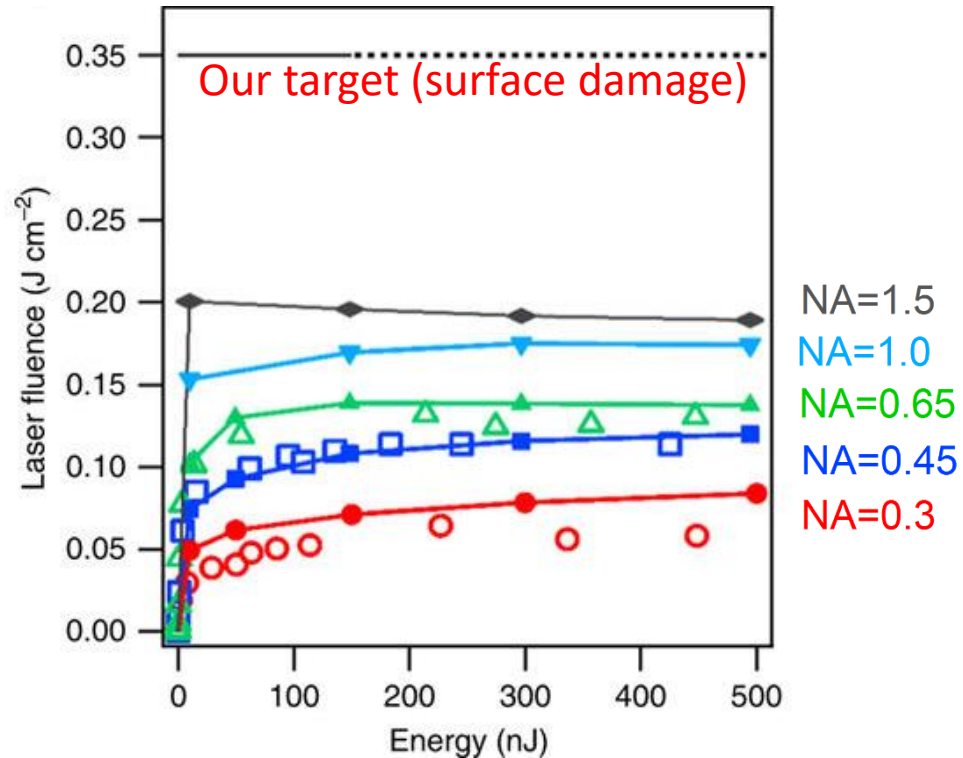
3D fluence distributions inside Si



Attempt to deliver a high fluence by increasing the pulse energy
energy fails and degrades resolution

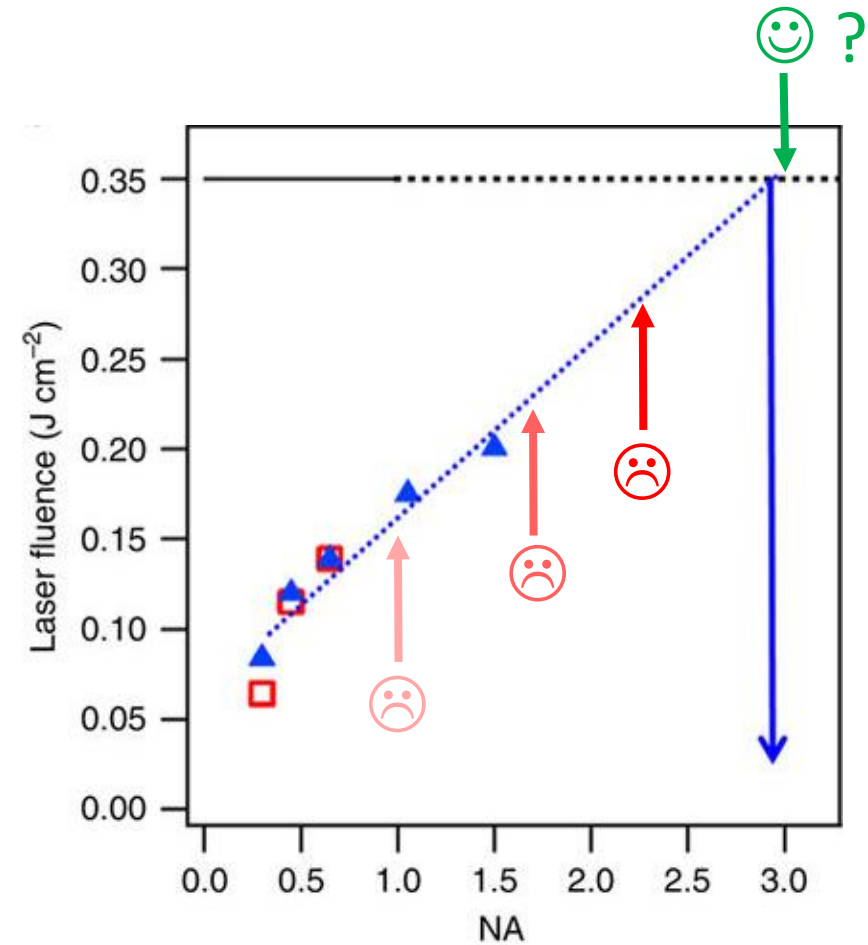
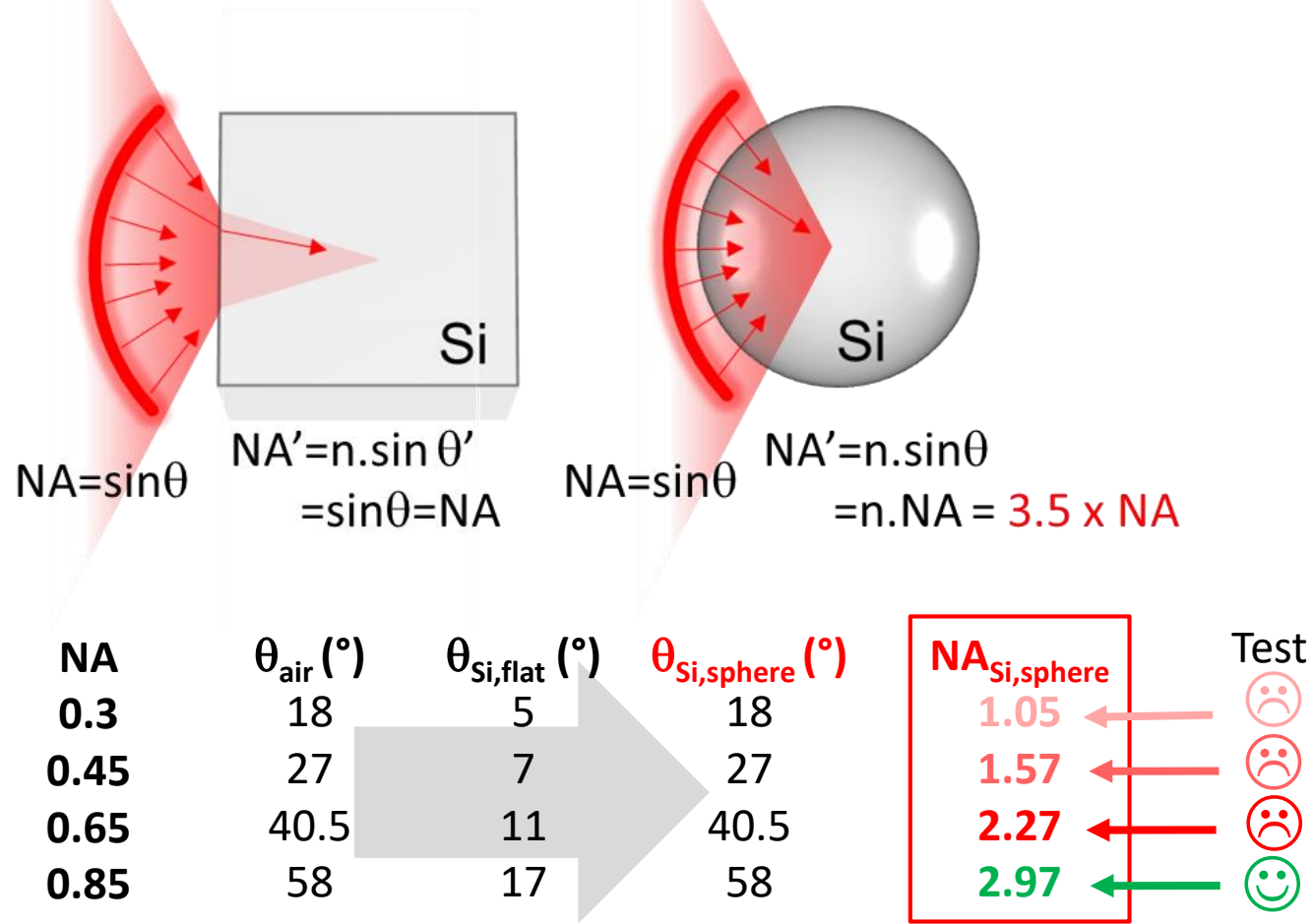
Solid immersion for increased delivered fluence

1300nm, 60fs



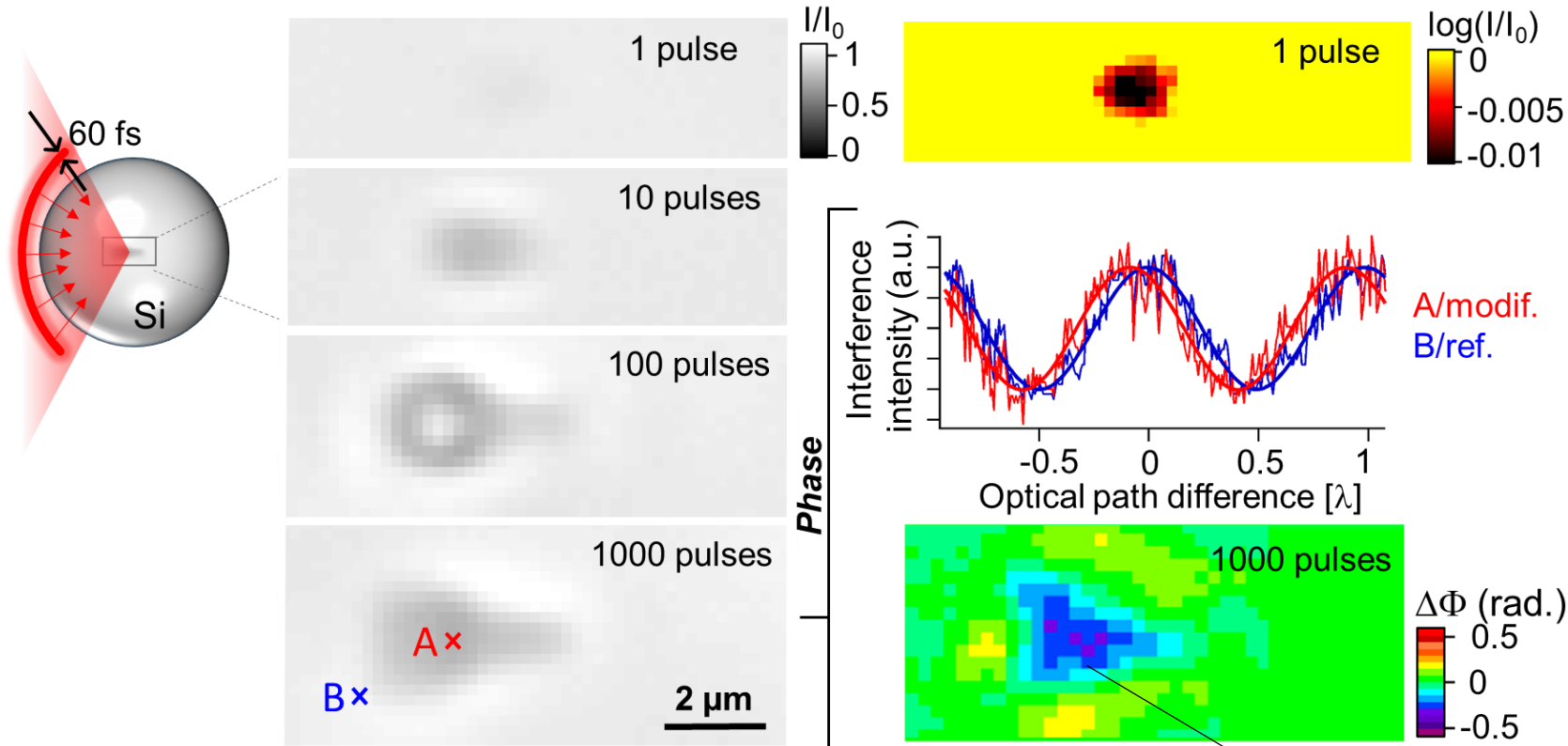
Extrapolating simulations and measurements, **hyper-NA values are required to circumvent sufficiently detrimental TPA and plasma pre-focal effects...**

Hyper-NA focusing as a solution ?



Extrapolating simulations and measurements, **hyper-NA values are required to circumvent sufficiently detrimental TPA and plasma pre-focal effects...**

Femtosecond laser refractive index modification



$\lambda=1300\text{nm}$

$NA=2.97$

60 fs

20nJ/pulse

$NA \approx 3$ leads to spot of
 $\lambda/6 \approx 220 \text{ nm}$ for $\lambda=1.3\mu\text{m}$

$\Delta n < 0 \neq$ amorphization

Infrared phase microscope: **Applied Optics** 55 (2016) 9577

Perspectives for ultrafast laser 3D writing with complex solid immersion lens (SIL) techniques ?

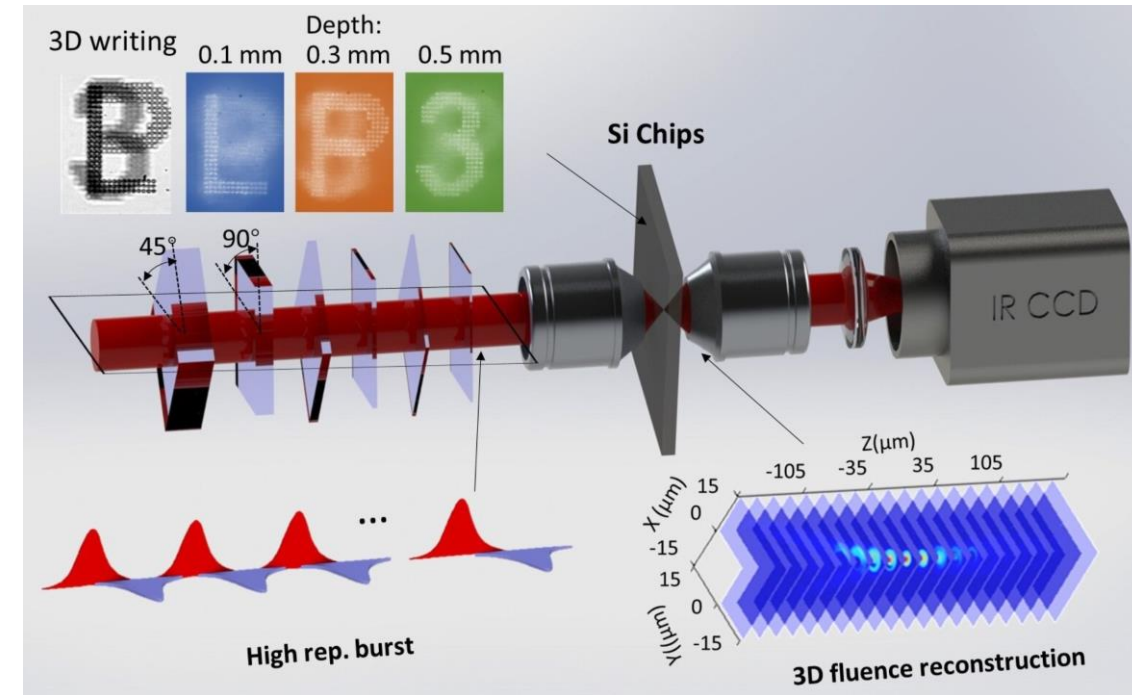
Crossing the threshold of ultrafast laser writing in bulk silicon, **Nature Communications** 8 (2017) 773

Outline – Ultrafast Laser Writing Deep inside Silicon

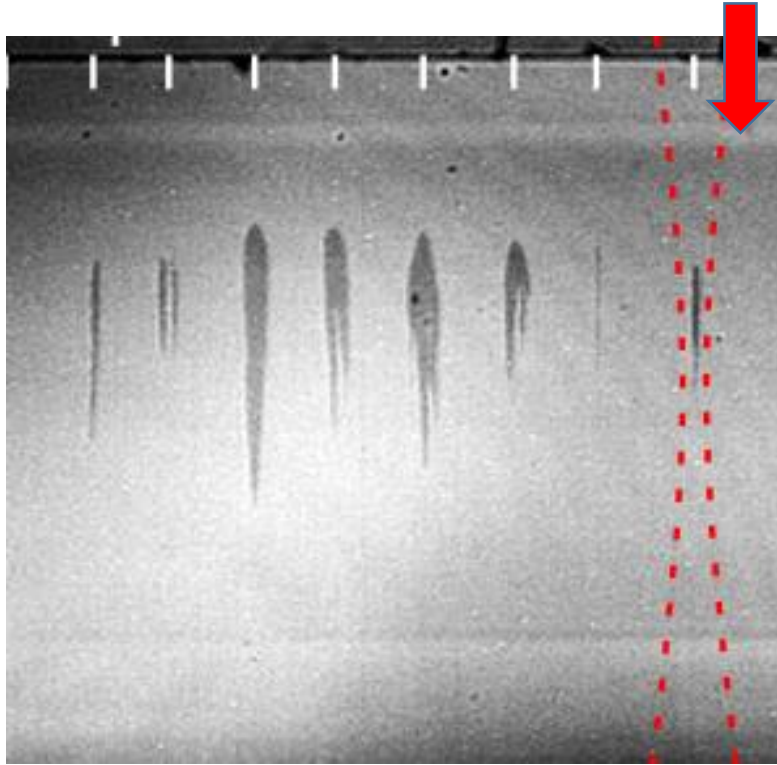
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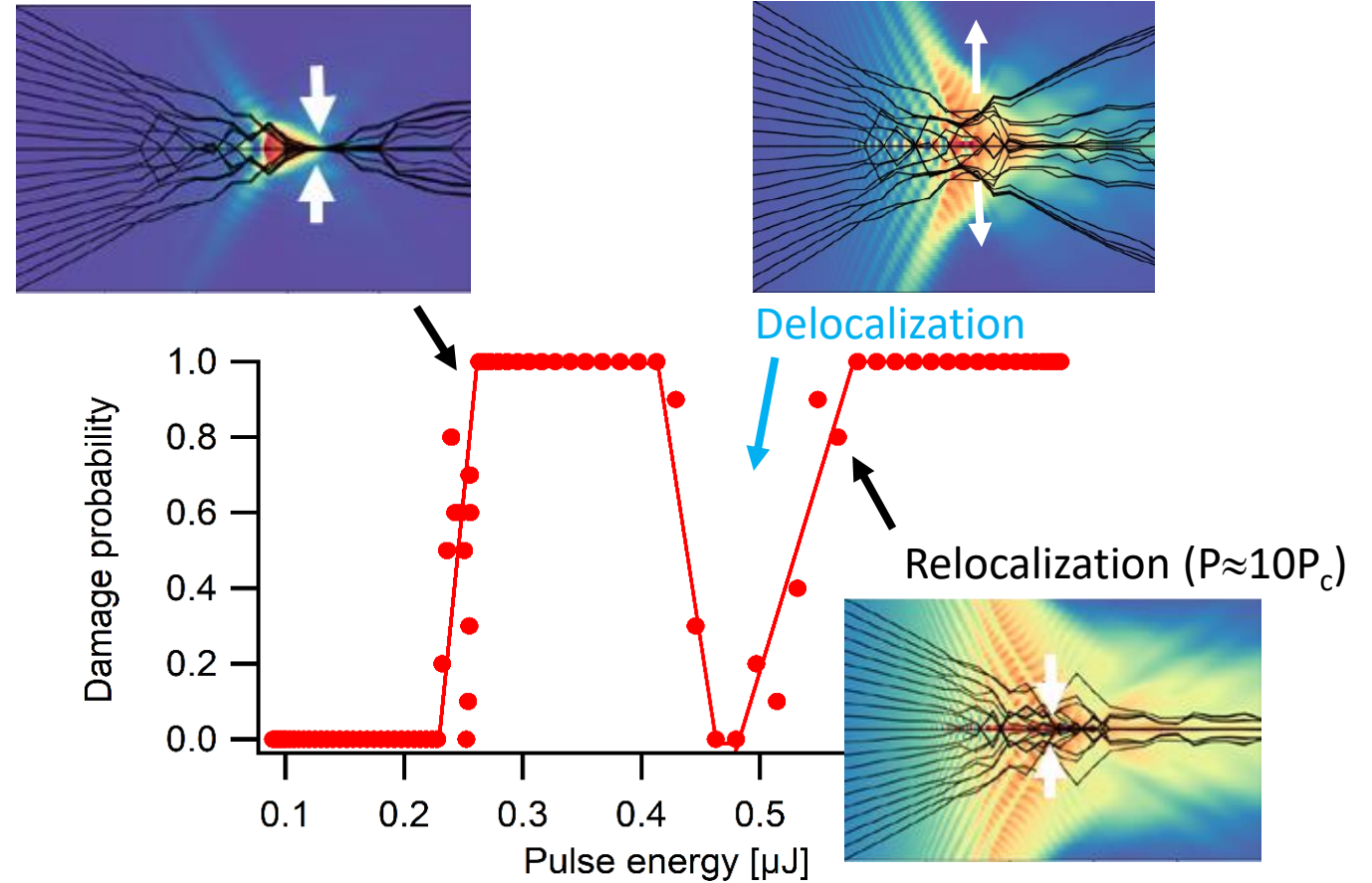


Controllability of the picosecond regime ?



1550 nm, NA=0.45, 10 ps

Applied Physics A 124 (2018) 302



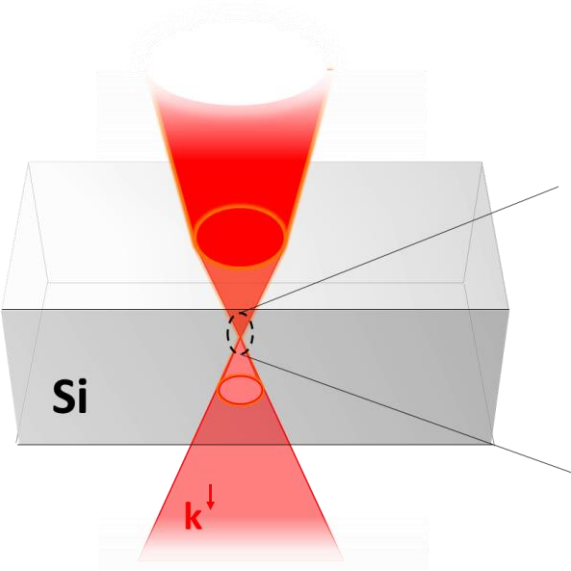
2000 nm, NA=0.85, 2 ps

Physical Review Applied 12 (2019) 024009

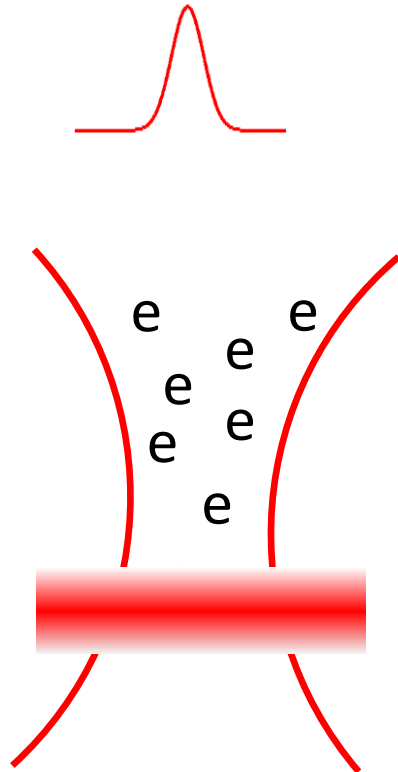
Competing nonlinear delocalization persists leading to hardly repeatable writing

+ Pulse duration dependence study: Optics Express 28 (2020) 26623

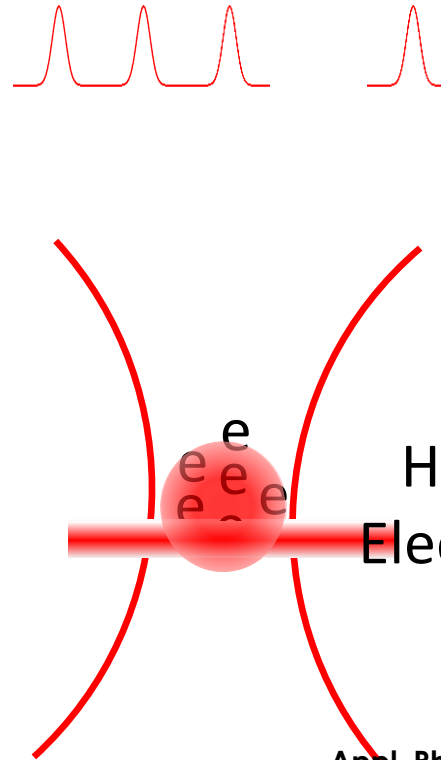
'Accumulation' strategy by ultrafast pulse trains



Single pulses



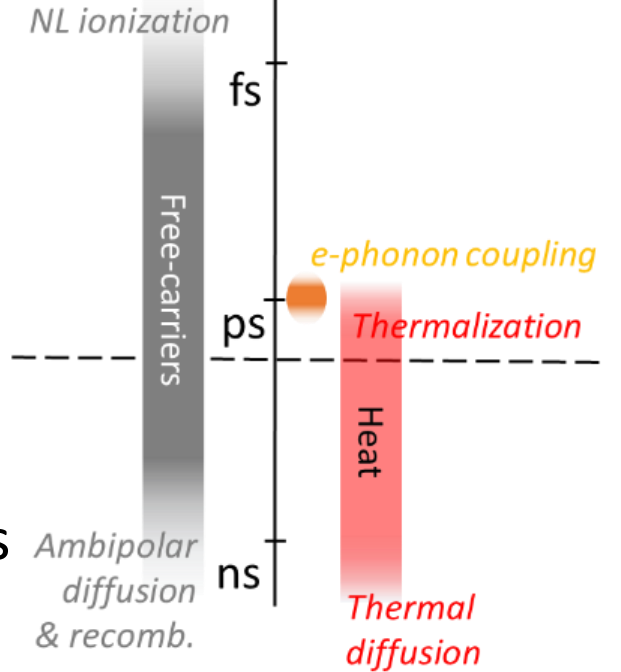
Train of pulses



Heat+
Electrons

Lifetime \approx 2.5ns (meas.)

Appl. Phys. Lett. 108 (2016) 041107



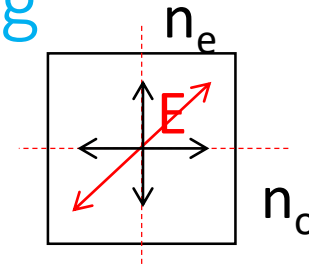
Dissipation (μm -region) \approx 10 ns (Eval. $D_{Si}=0.86 \text{ cm}^2/\text{s}$)

>GHz pulses must enable localized accumulation of heat and electrons near focus

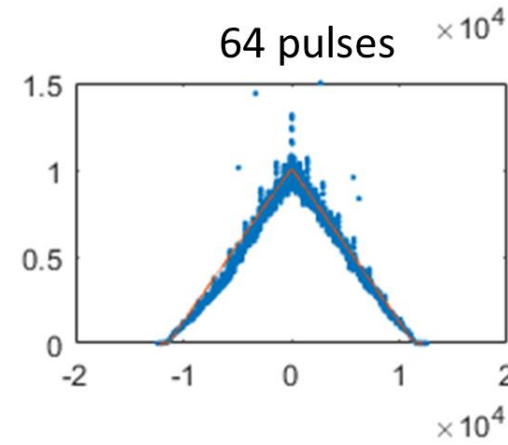
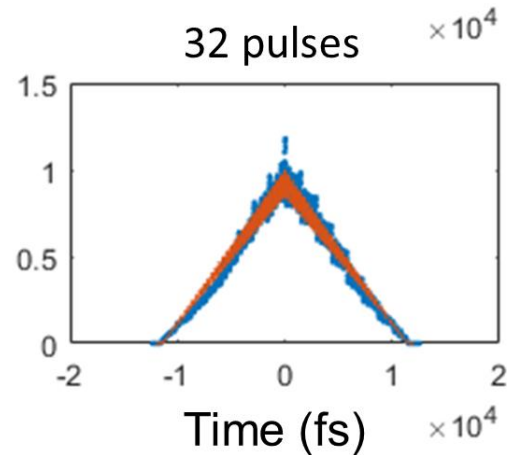
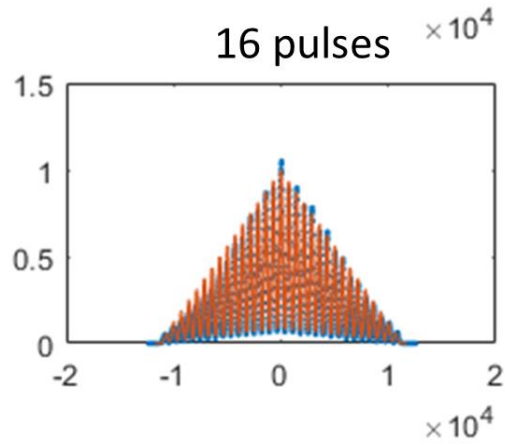
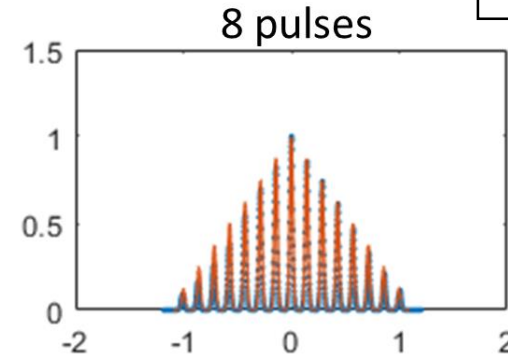
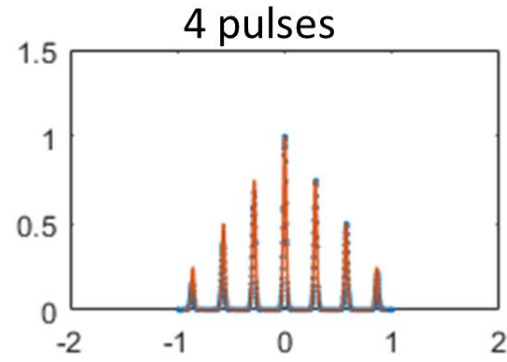
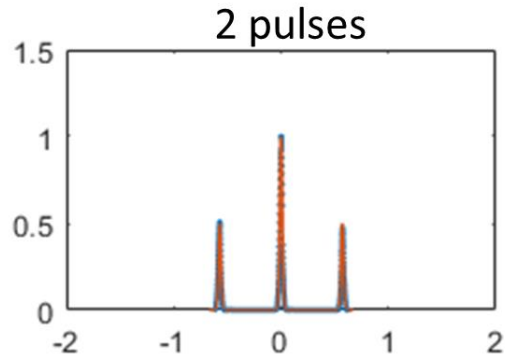
Ultrafast Laser Writing Deep Inside Silicon with THz-repetition-rate Trains of Pulses, **Research** 2020 (2020) 8149764, <https://doi.org/10.34133/2020/8149764>

Ultrafast trains of pulses by polarization splitting

$\lambda=1550\text{nm}$
 $\tau_{\text{pulse}}=200\text{fs}$



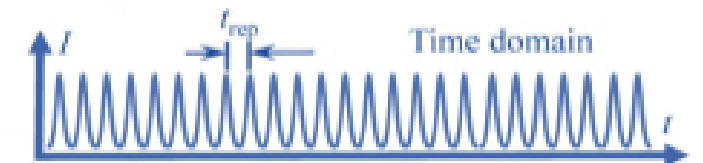
Auto-correlation signal



Delay determined by thickness

YVO ₄ Crystal Thickness(mm)	Theoretical Delay(ps)
0.25	0.17
0.5	0.34
1	0.68
2	1.36
4	2.73
8	5.47

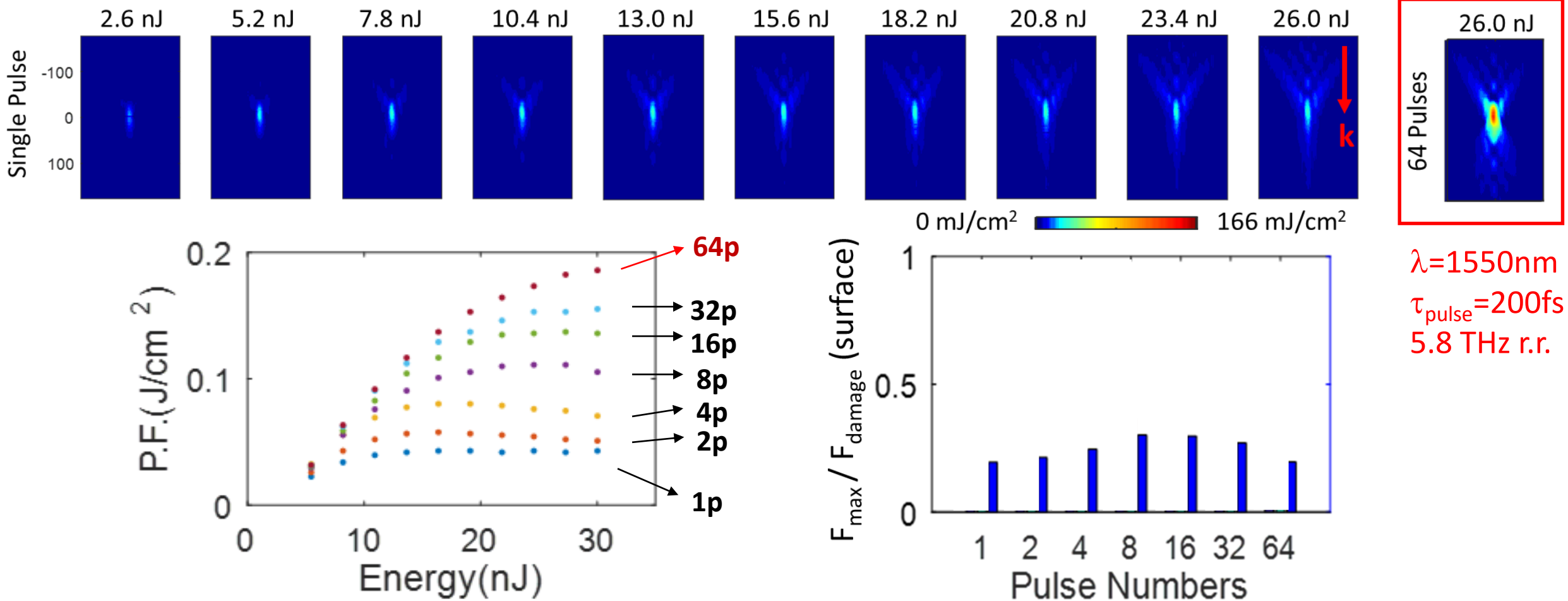
$2^6=64$ pulses



5.8 THz rep. rate trains of up to 64 pulses by passive propagation in a stack of crystals

Ultrafast Laser Writing Deep Inside Silicon with THz-repetition-rate Trains of Pulses, **Research** 2020 (2020) 8149764, <https://doi.org/10.34133/2020/8149764>

Improved energy densities to achieve writing



Improved conditions (+60%) in Si for burst irradiation
 optimum with \approx 8-16 pulses but still below bulk damage threshold

Ultrafast Laser Writing Deep Inside Silicon with THz-repetition-rate Trains of Pulses, **Research** 2020 (2020) 8149764, <https://doi.org/10.34133/2020/8149764>

Burst-induced modifications deep inside Si

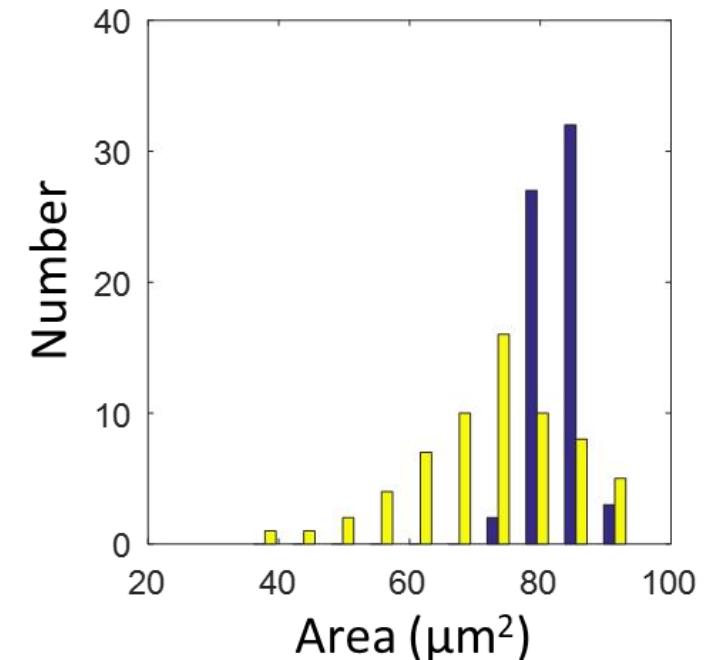
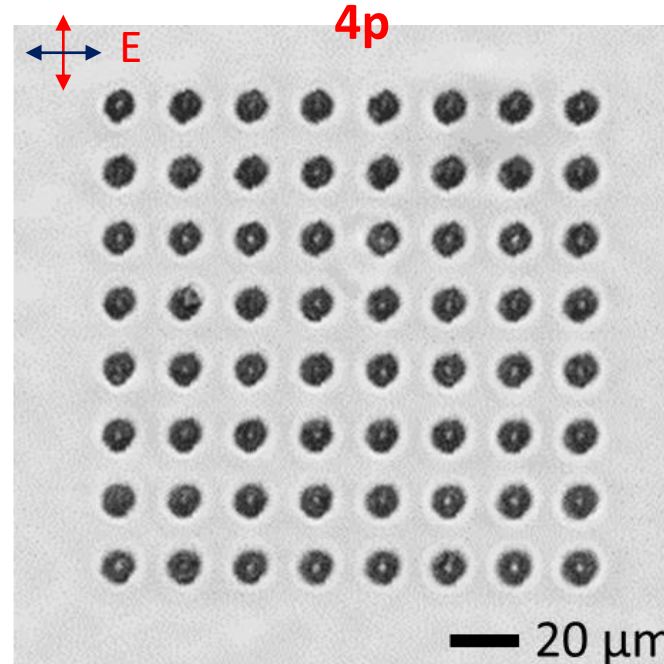
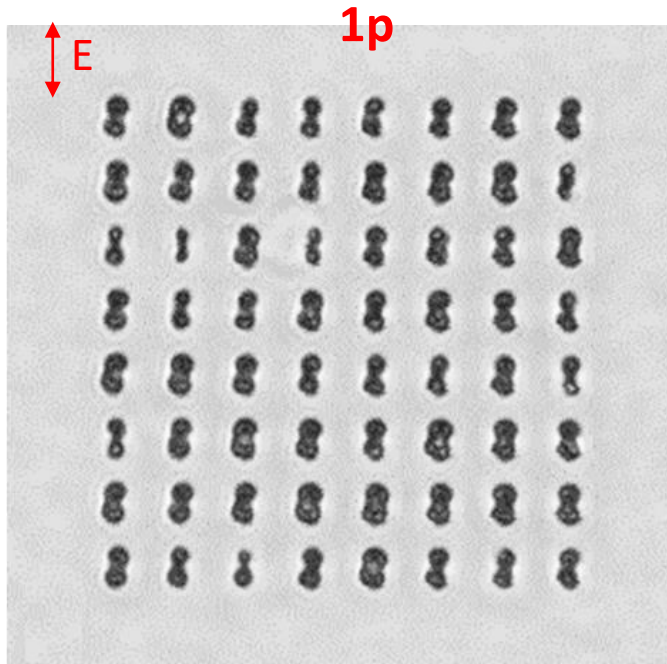
0.2 ps
(5.8 THz)



5 ps
(0.37 THz)



6.7 ps
(0.37 THz)



'Accumulation' burst strategy is **beneficial for crossing threshold and/or stabilize writing**

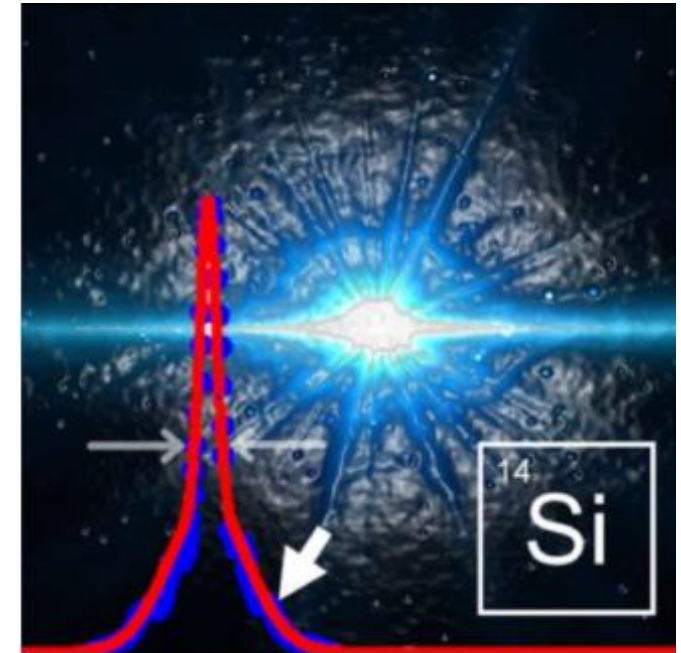
Ultrafast Laser Writing Deep Inside Silicon with THz-repetition-rate Trains of Pulses, **Research** 2020 (2020) 8149764, <https://doi.org/10.34133/2020/8149764>

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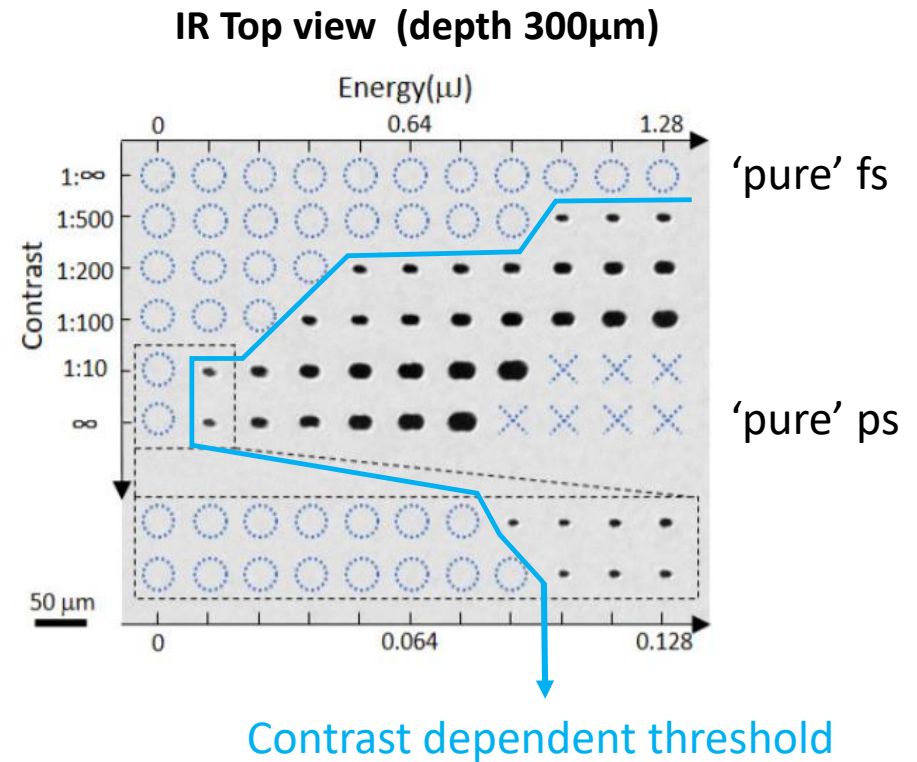
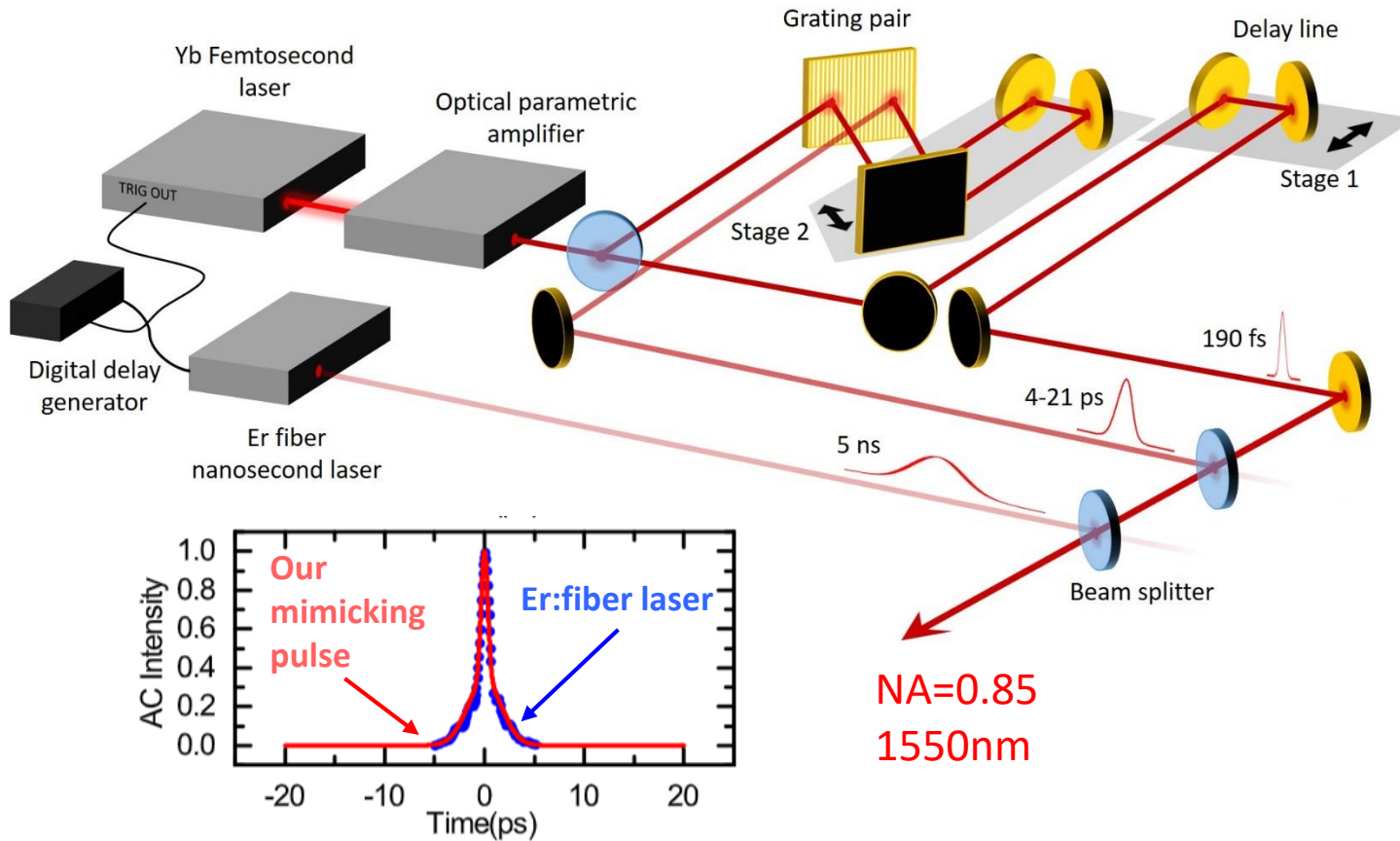
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Multi-time scale control of the temporal contrast

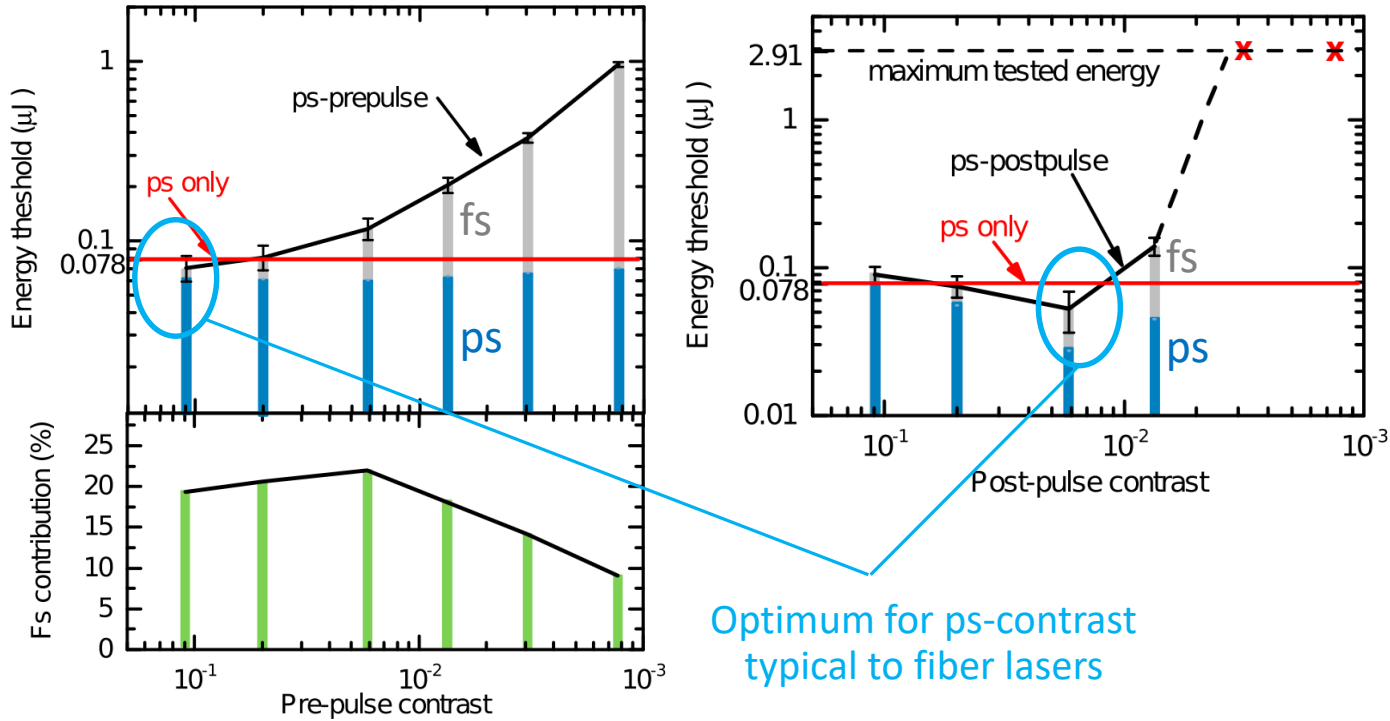


Imperfect contrast (e.g. fiber lasers) leading to **modifications**
inaccessible with highly contrasted pulses (eg. OPA)

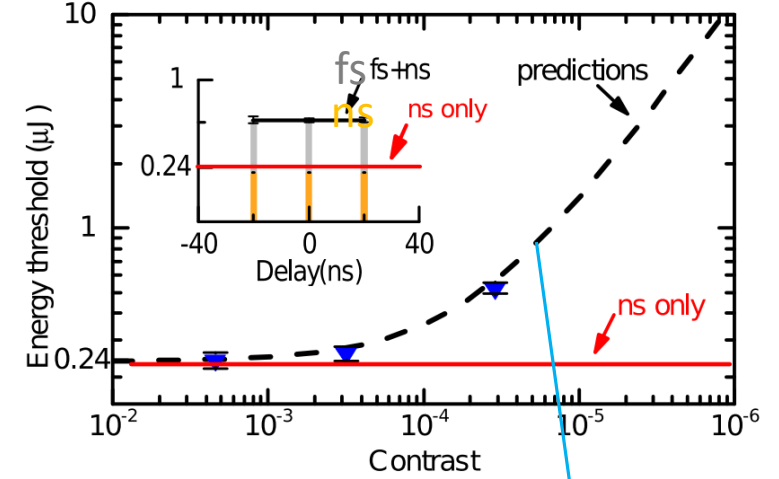
Temporal Contrast Imperfections as Drivers for Ultrafast Laser Modifications in Bulk Silicon, *Physical Review Research* 2 (2020) 033023

Multiscale temporal contrast study

Picosecond contrast (190 fs + 11ps, delay ±20ps)



ns contrast (190 fs + 5ns)



Pure ns modification in all cases indicating typical ns ASE in fs lasers can always induce modification... without any ultrafast contribution

An unusually high sensitivity to the temporal contrast

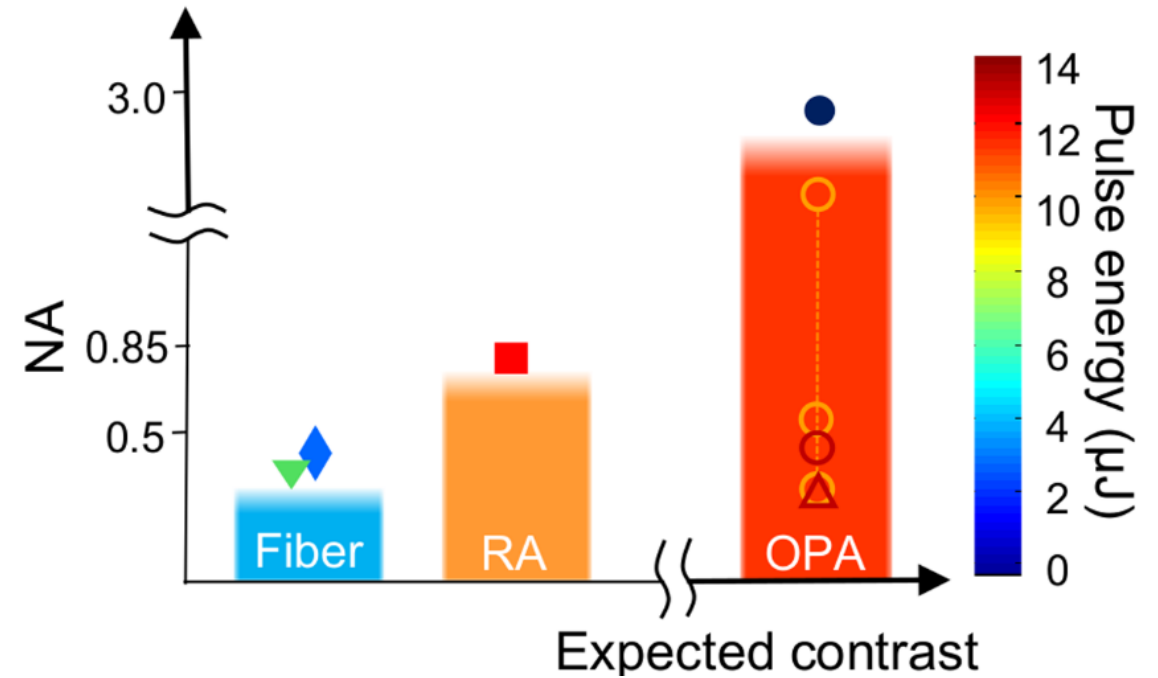
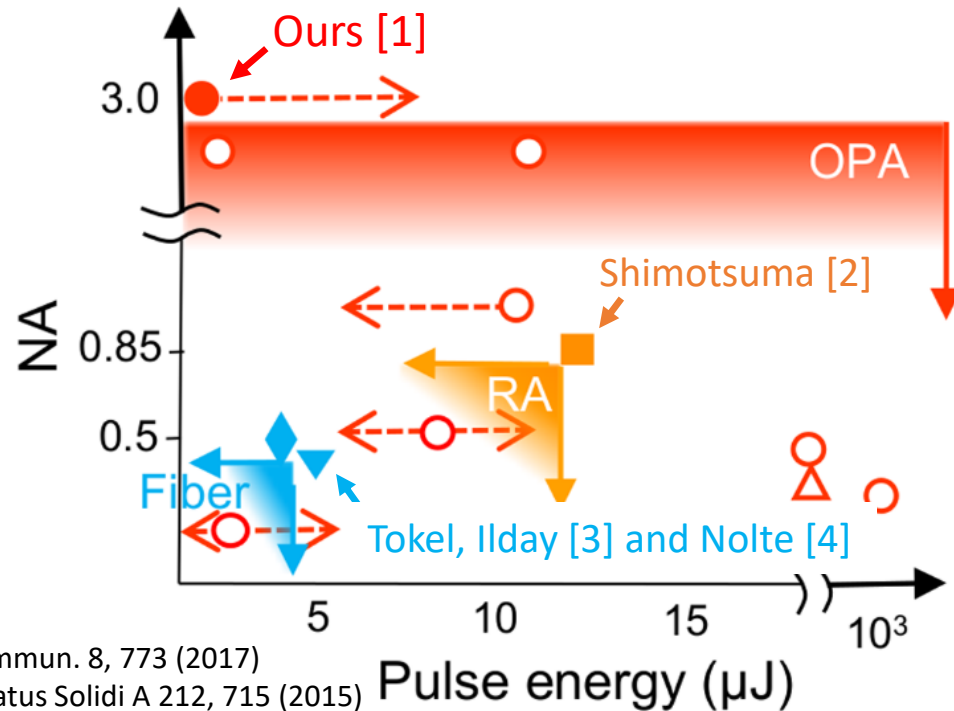
... leading to a laser technology dependent problem ?

Solving contradictions between previous work

Si Bulk Modifications attempts (sub-ps)

Solid symbol: Successful ☺

Empty symbols: Unsuccessful ☹



[1] Nat. Commun. 8, 773 (2017)

[2] Phys. Status Solidi A 212, 715 (2015)

[3] Appl. Phys. A-Mater. 124, 302 (2018)

[4] Opt. Lett. 42, 3028 (2017)

A laser-technology dependent problem: contrast imperfections are drivers for modifications

... inspiring new developments based on temporal shaping for reliable 3D writing in Si

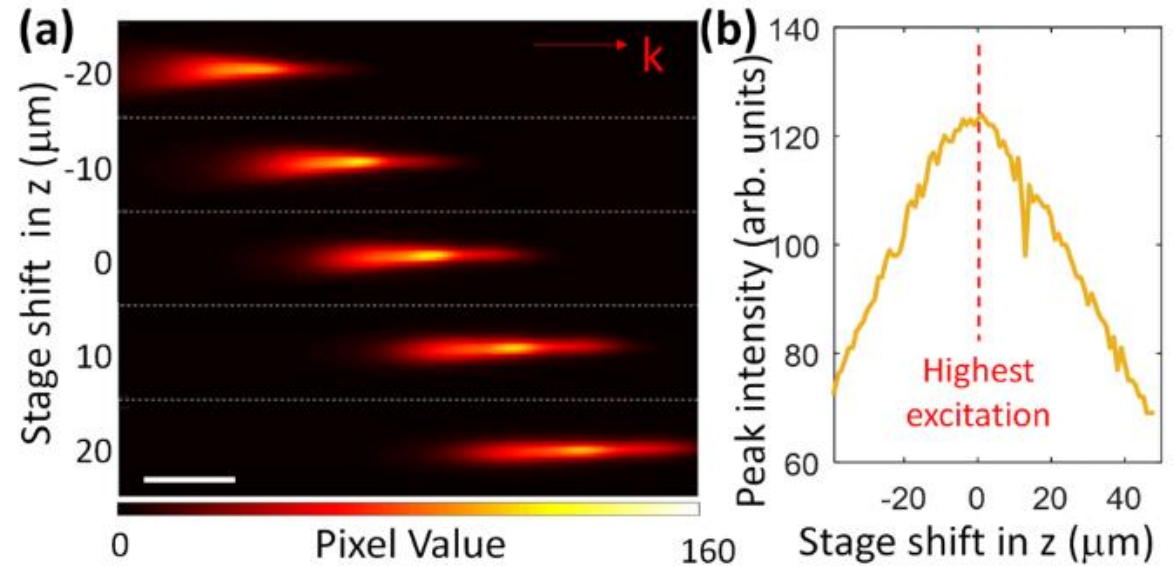
Temporal Contrast Imperfections as Drivers for Ultrafast Laser Modifications in Bulk Silicon, **Physical Review Research** 2 (2020) 033023

In-volume laser direct writing of silicon – Challenges and Opportunities, **Laser and Photonics Reviews** (2021) 2100140

Today's performance with multi-time scale control

Image removed

Real time monitoring of ionization by luminescence



... Quantitative plasma characterization in bulk semiconductors,
Applied Physics Letters 119 (2021) 041108

Improved resolution and controllability (incl. progressivity and erasure)

....using pre-ionization pulses and giving new perspectives !

Patent Application EP21 184898.1 (2021)

Acknowledgements...

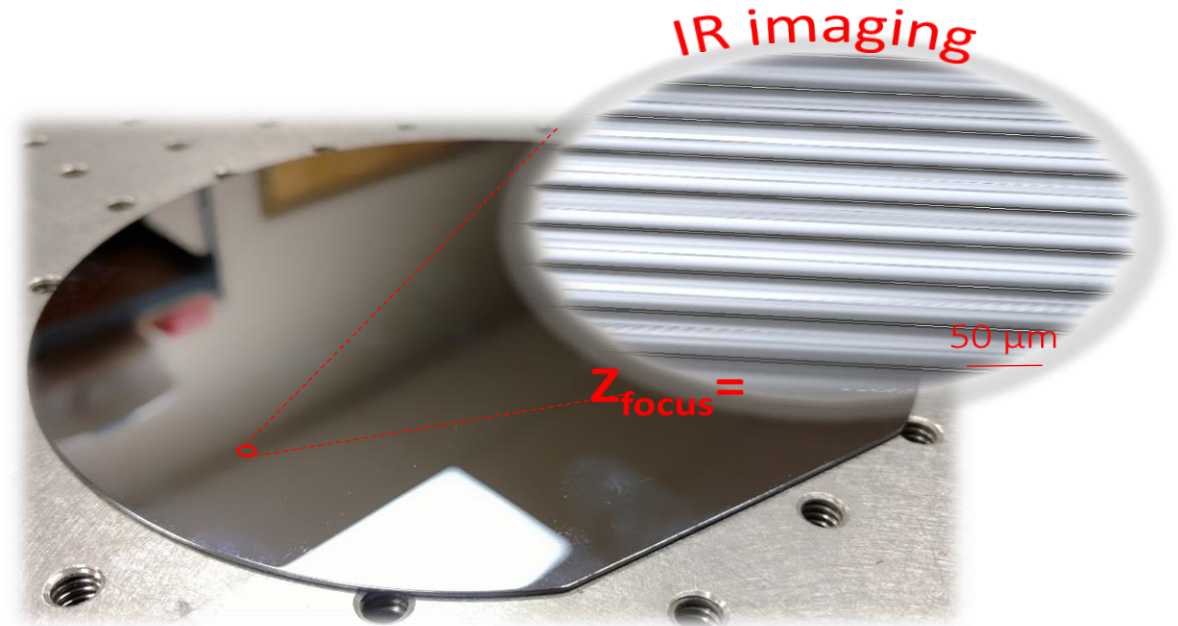


Stephanie Leyder (PhD)
 Margaux Chanal (PhD)
Amlan Das (PhD)
 Alexandros Mouskeftaras
 Maxime Chambonneau
Andong Wang
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 Georges Gebryel El Reaidy
Pol Martinez Sopena
 Haoqing Ning
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 Sambit Mitra (MSc, KIT Germany)
 Raphaël Clady
 Philippe Delaporte
 Marc Sentis
 Nicolas Sanner
 Olivier Utéza
 Jörg Hermann

Int'l Associated Laboratory



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